

High precision integrated circuit capacitors

ABSTRACT OF THE INVENTION

5 A polysilicon layer (30) is formed on a dielectric region (20). An optional metal silicide layer (50) can be formed on the polysilicon layer. A dielectric layer (60) is formed over the metal silicide layer and a conductive layer (70) formed over the dielectric layer. The formed layers are etched by a combination
10 of multi-step dry and wet process to form high precision integrated circuit capacitors.